

High-Voltage SiC Optimized for Megawatt Charging in EV Long-haul Trucking



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A New World Needs New EV Trucks



MAN Truck & Bus and ABB E-mobility, exclusive cooperation agreement. Jan '24 ⁽²⁾

Passenger EV adoption increasing:

USA: passenger EV forecast for 2030 up >2x⁽¹⁾

Long-haul EV trucking: early days

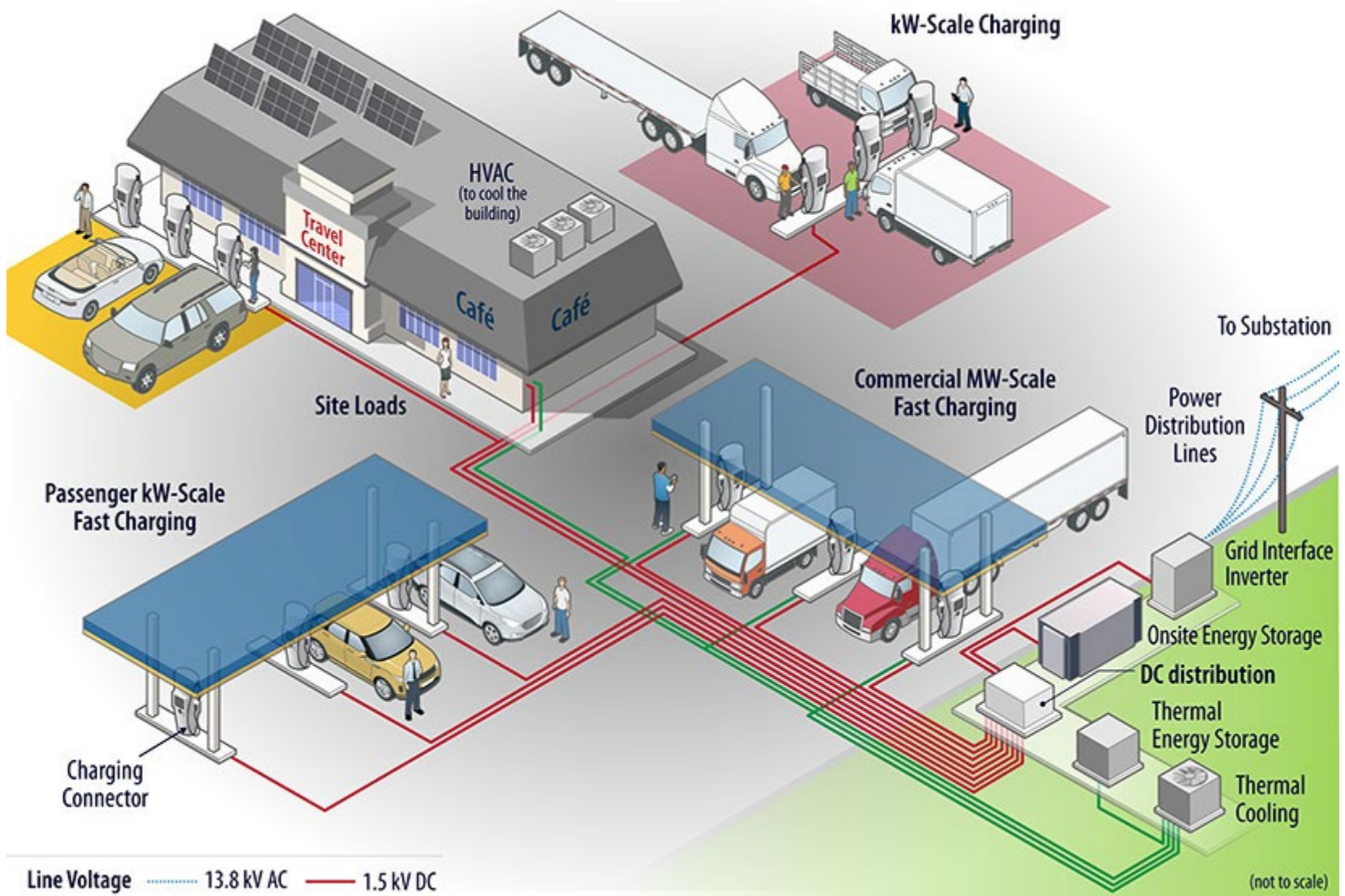
In 2022, 60k medium- and heavy-duty BEV trucks sold (~1% of total), 110 BEV truck models introduced

US and 26 other countries signed COP27 MoU:
30% ZEV sales by 2030 and 100% by 2040

1) Boston Consulting Group (BCG) forecasts, 21% in 2018, 53% in 2022 forecast

2) <https://press.mantruckandbus.com/corporate/megawatt-charging-and-more-man-and-abb--e-mobility-announce-rd-cooperation/>

Roadside Charging: Many HV SiC Opportunities



Nikola BEV vs H2 Fuel Cell



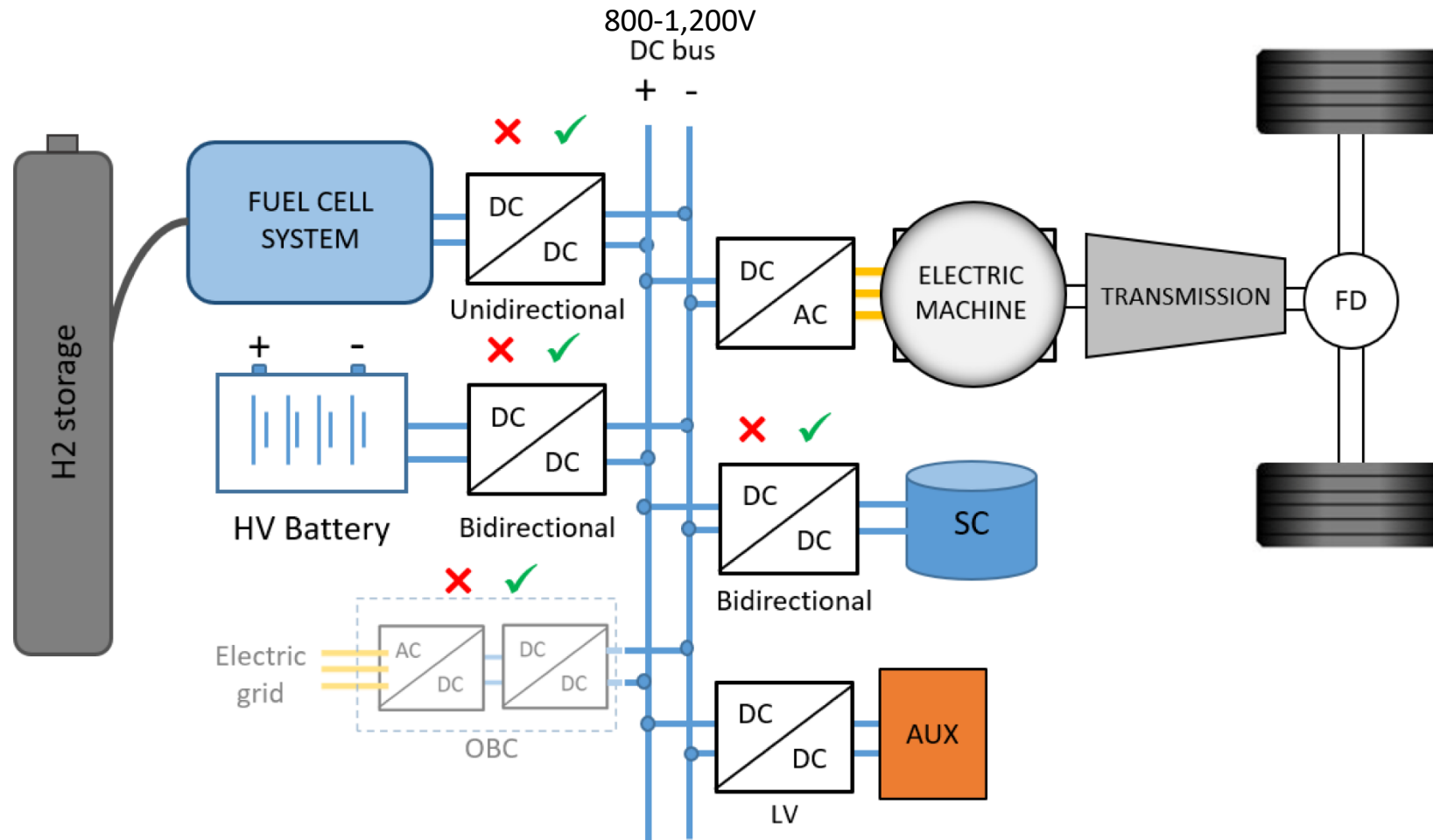
Spec	Nikola BEV ⁽¹⁾	Nikola Fuel-Cell ⁽²⁾
Max Speed (mph)	70	70
Range (miles)	Up to 330	Up to 500
Battery (kWh)	733	164
Fuel Cell Power Module (kWh)	-	200
Continuous Power (kW)	480	400
Instantaneous Power (kW)	797	575
Charging / Refueling Time (mins)	90 (@350 kW) << @ 1MW?	20

1) <https://nikolamotor.com/the-nikola-tre-bev-reinventing-short-haul-transportation/>

2) <https://nikolamotor.com/tre-fcev/>



Hydrogen Fuel-cell: Still More Power, Still High Voltage



Full BEV: More Power, Higher Voltage

“Megawatt Charging System”: SAE J3271^(1,2), up to 3.75 MW via 1,250 V cable

DC Fast-Charger Specifications	Passenger / LDV	HDV J3721 (non-cooled)	HDV J3721 (actively-cooled)
Power (max, kW)	350	440	3,750
Voltage (max, V)	920	1,250	1,250
Current (max, A)	500	350	3,000
Vehicle Battery (nom, V)	400 / 800	800, 1200	800, 1200
SiC Device Voltage (nom, V)	750 / 1,200	1,200 / 1,700	1,700



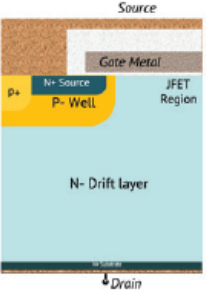
1) SAE J3271 specification, <https://standardsworks.sae.org/standards-committees/j3271-megawatt-charging-system-electric-vehicles-tf>

2) <https://www.anl.gov/reference/faq-charging-for-heavyduty-electric-trucks>



The Planar Problem

Planar



Manufacturability

- » Repeatable
- » High yield
- » Low cost

Performance

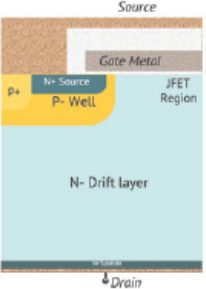
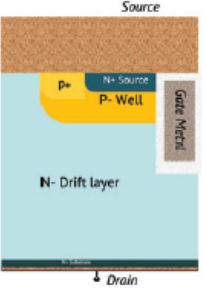
- » High $R_{DS(ON)}$ / area
- » Slow switching
- » High $R_{DS(ON)}$ / Δ temp

Reliability

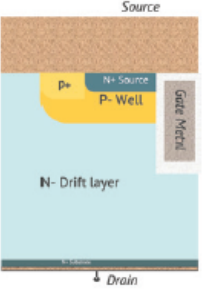
- » Rugged gate oxide (stable V_{TH})



The Trouble with Trench

	 <p>Planar</p>	 <p>Trench</p>
Manufacturability	<ul style="list-style-type: none"> » Repeatable » High yield » Low cost 	<ul style="list-style-type: none"> » Inconsistent trench etch » Lower yields » High cost
Performance	<ul style="list-style-type: none"> » High $R_{DS(ON)}$ / area » Slow switching » High $R_{DS(ON)}$ / Δ temp 	<ul style="list-style-type: none"> » Lower $R_{DS(ON)}$ / area » Faster switching » High $R_{DS(ON)}$ / Δ temp
Reliability	<ul style="list-style-type: none"> » Rugged gate oxide (stable V_{TH}) 	<ul style="list-style-type: none"> » Failures due to non-uniform gate oxide » Lower short-circuit capability

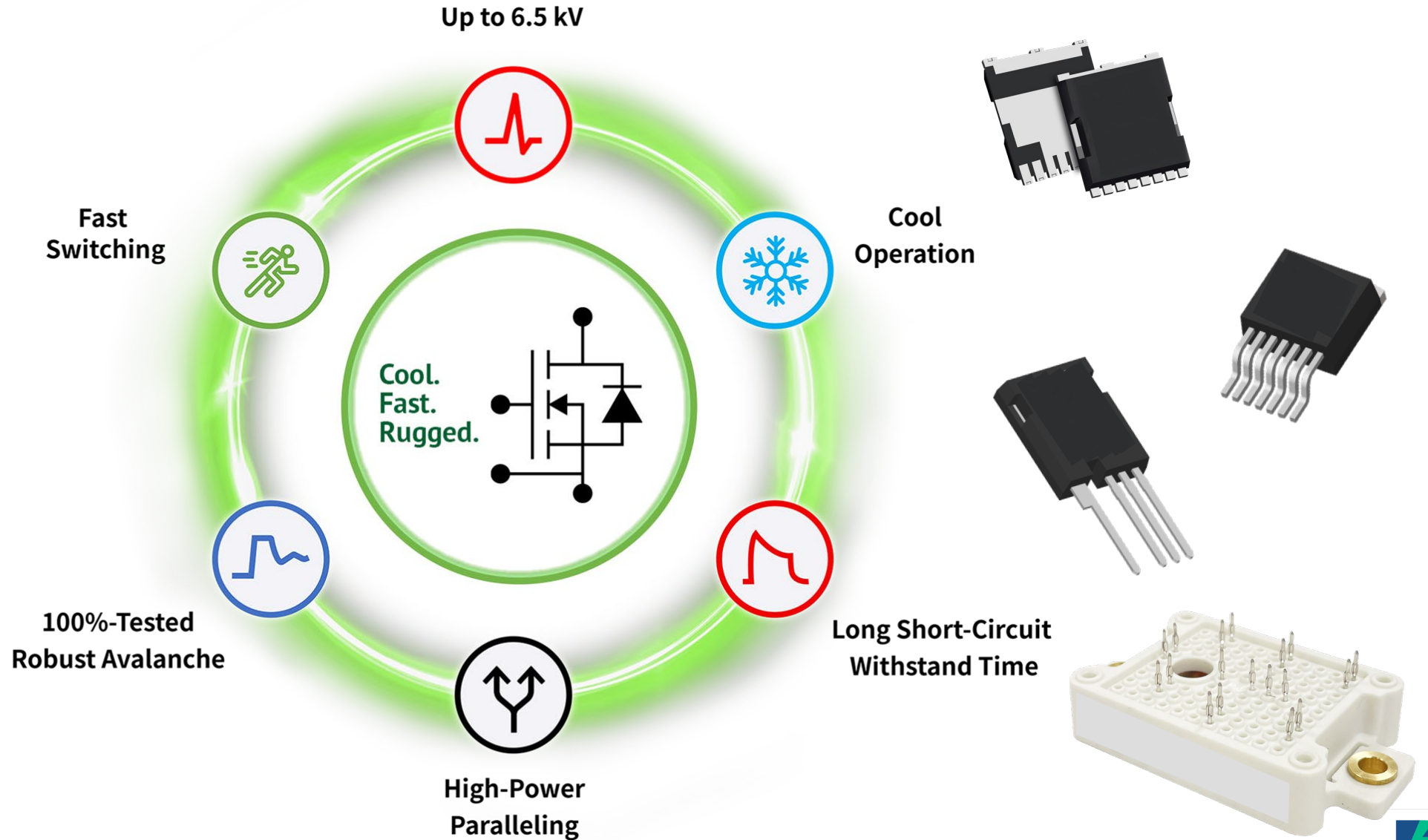
Best of Both: Trench-Assisted Planar Gate

	<p>Planar</p> 	<p>Trench</p> 	<p>Trench-Assisted Planar Gate</p> 
Manufacturability	<ul style="list-style-type: none"> » Repeatable » High yield » Low cost 	<ul style="list-style-type: none"> » Inconsistent trench etch » Lower yields » High cost 	<ul style="list-style-type: none"> » Repeatable » High yield » Low cost
Performance	<ul style="list-style-type: none"> » High $R_{DS(ON)}$ / area » Slow switching » High $R_{DS(ON)}$ / Δ temp 	<ul style="list-style-type: none"> » Lower $R_{DS(ON)}$ / area » Faster switching » High $R_{DS(ON)}$ / Δ temp 	<ul style="list-style-type: none"> » Lower $R_{DS(ON)}$ / area » Fastest switching » Lowest $R_{DS(ON)}$ / Δ temp
Reliability	<ul style="list-style-type: none"> » Rugged gate oxide (stable V_{TH}) 	<ul style="list-style-type: none"> » Failures due to non-uniform gate oxide » Lower short-circuit capability 	<ul style="list-style-type: none"> » Highest 100% tested avalanche » Long short-circuit withstand time » Rugged gate oxide (stable V_{TH})

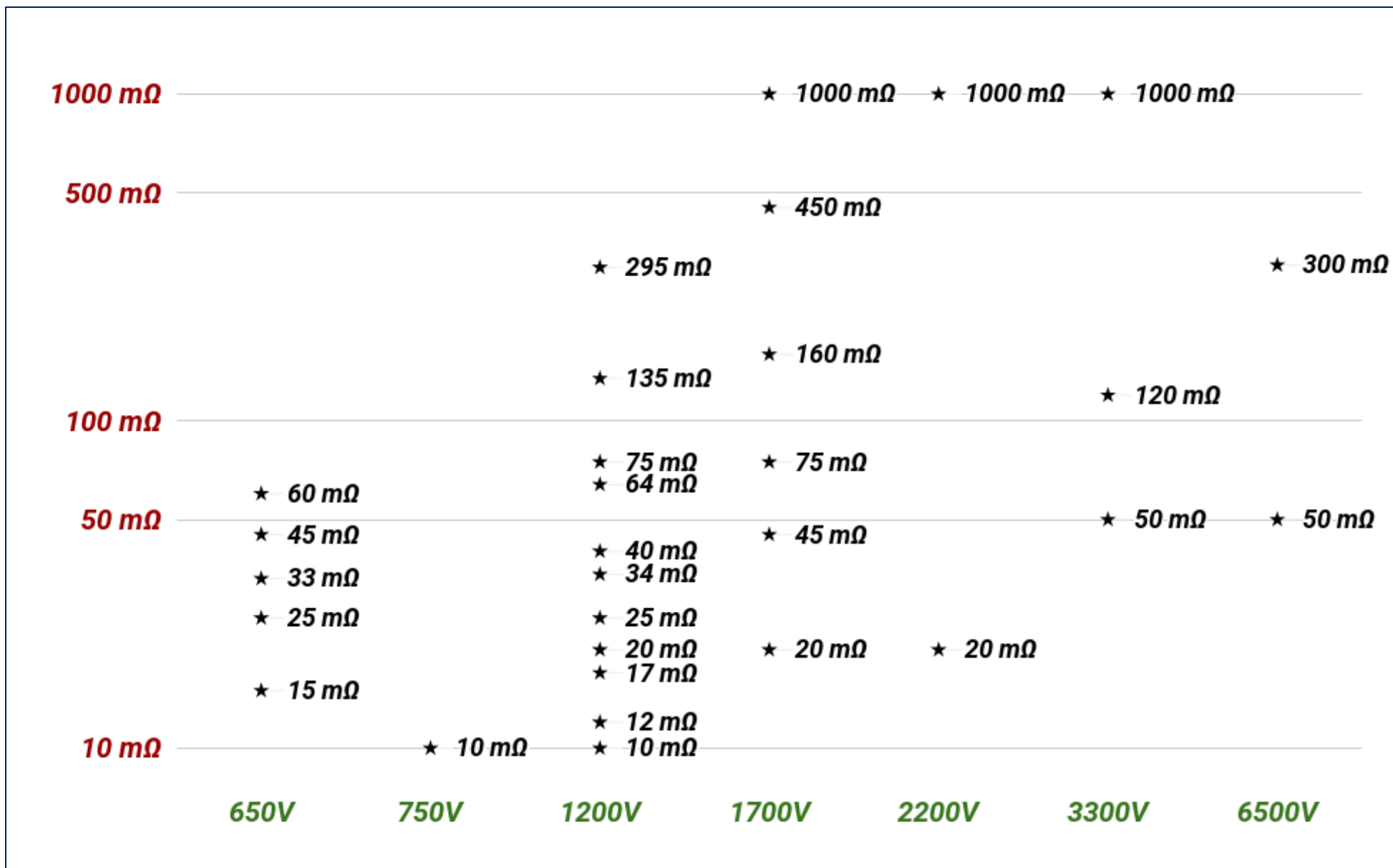


Highest Performance, Voltage Range & Ruggedness

Patented Trench-Assisted Planar-Gate SiC MOSFETs



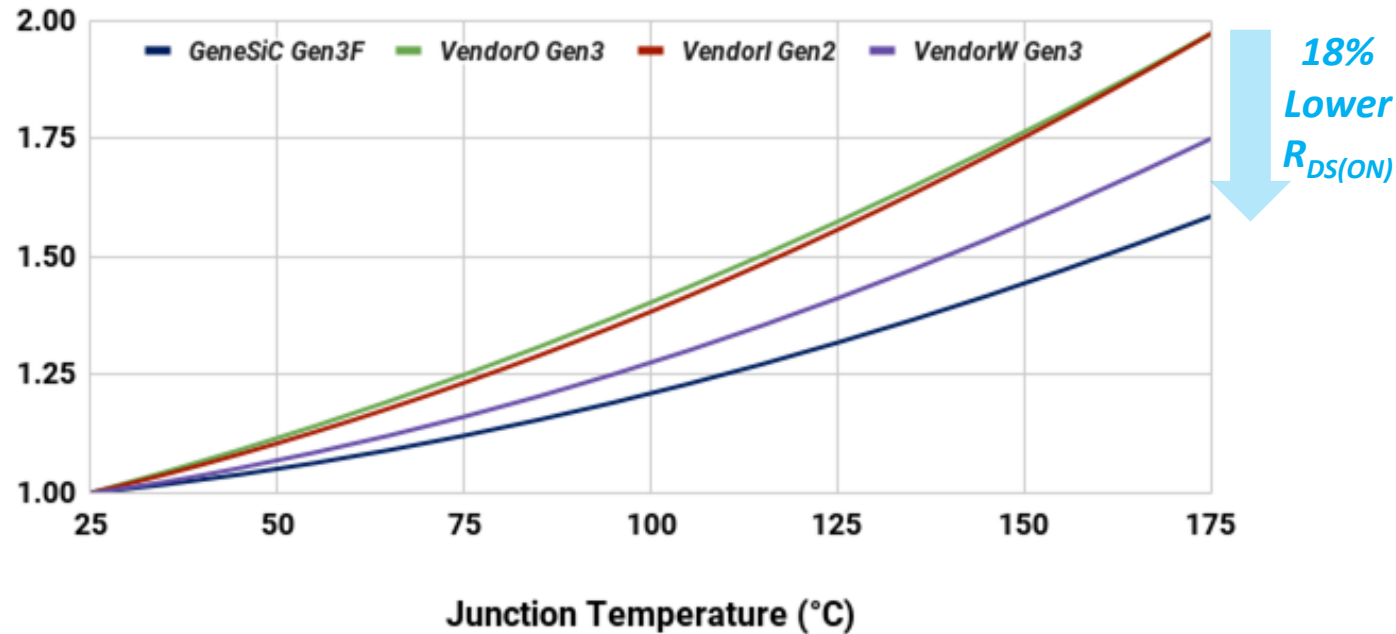
Broad SiC Portfolio (650 V → 6,500 V)



Trench-Assisted Planar Gate Performance

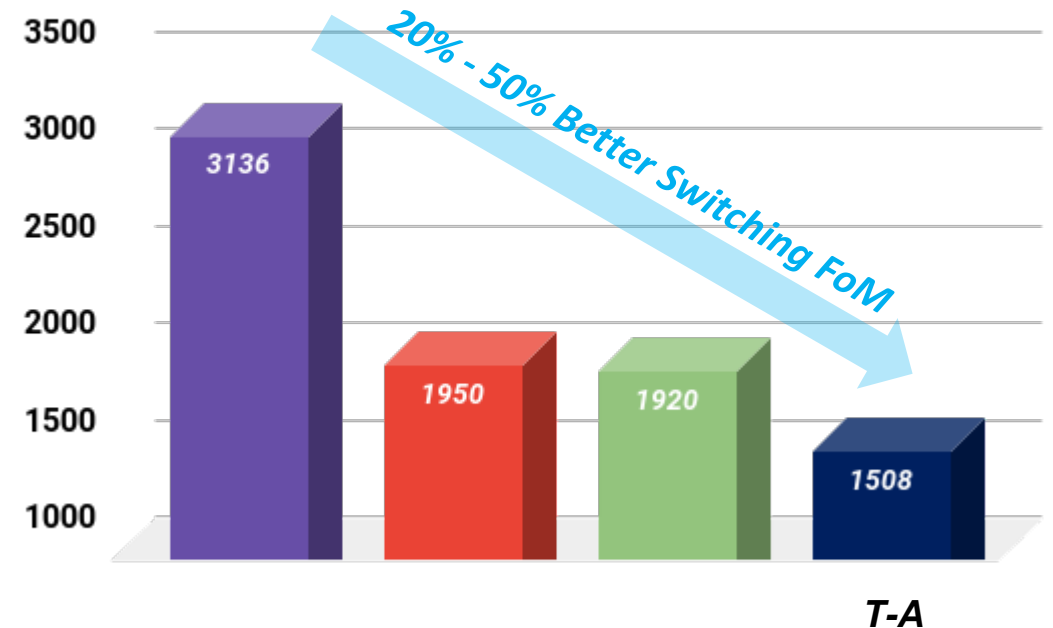
Static Performance (1200 V)

On-Resistance vs. Temperature



Switching Performance (1200 V)

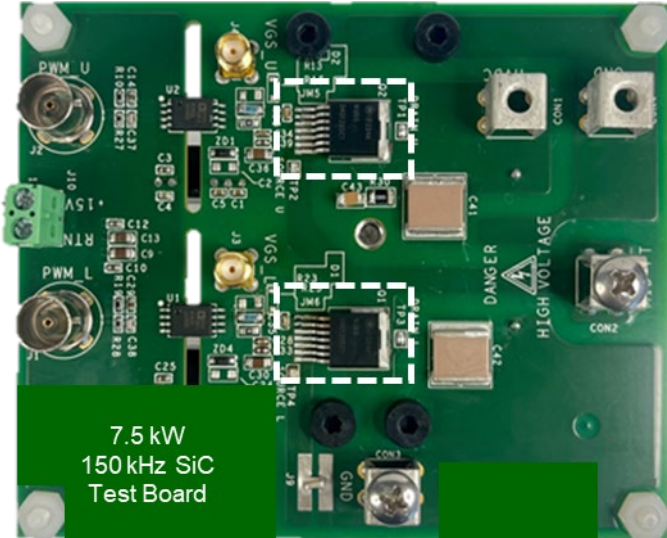
$R_{ON} \times E_{OSS}$ at 125°C (mΩ-μJ)



- ❑ *Tr*-assisted planar gate offers 10% -18% lower on-resistance at 175°C
- ❑ 20% - 50% better switching figure-of-merit
- ❑ Enables lower losses and cooler operation
 - ✓ Better system efficiency
 - ✓ Longer lifetime

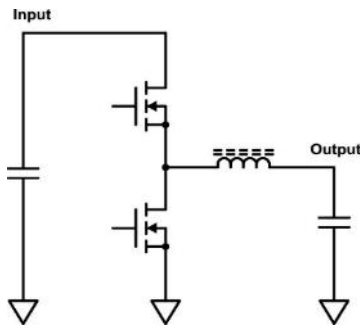


Faster, Cooler, Longer Lifetime

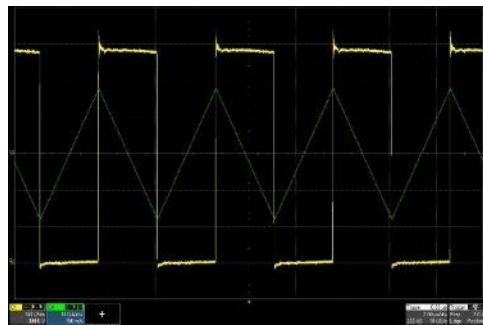


Test Board

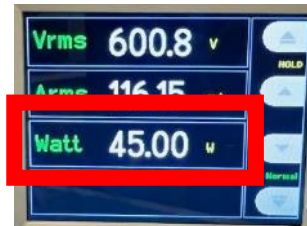
- Trench-assisted planar FET vs. Competitor SiC FET
 - 1,200 V, 40 mΩ, D2pak in half-bridge
 - Represents 7.5 kW DC-DC converter (e.g. data center, EV)
 - 150 kHz switching = ~10x faster than Si IGBT example
- **>80% energy savings (>3,000 kWh/yr) vs Si IGBTs**
-25°C cooler = 3x longer life vs other SiC
(reduced maintenance / repair costs)



Test Circuit
(1-phase of 3-phase motor drive)



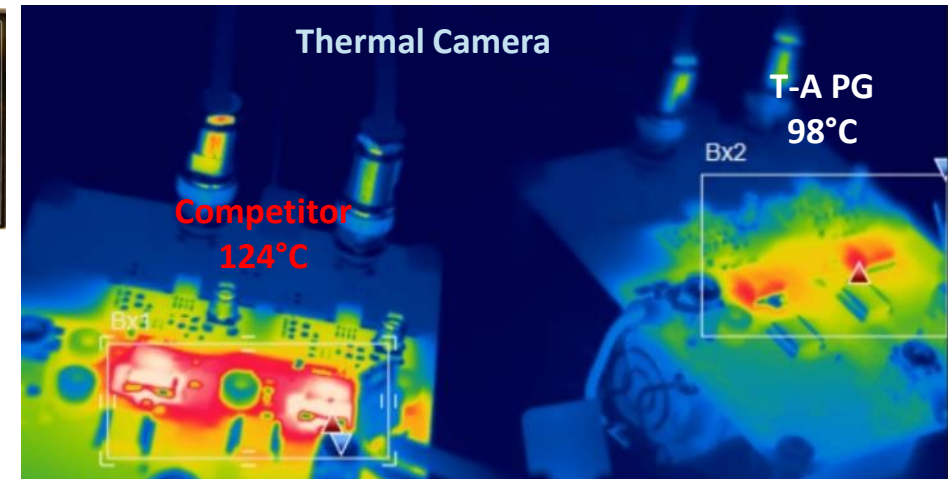
Switching Waveforms
(40 A pk-pk, 20 A turn-off)



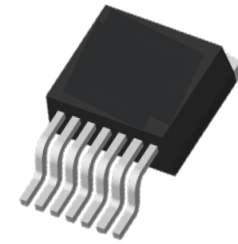
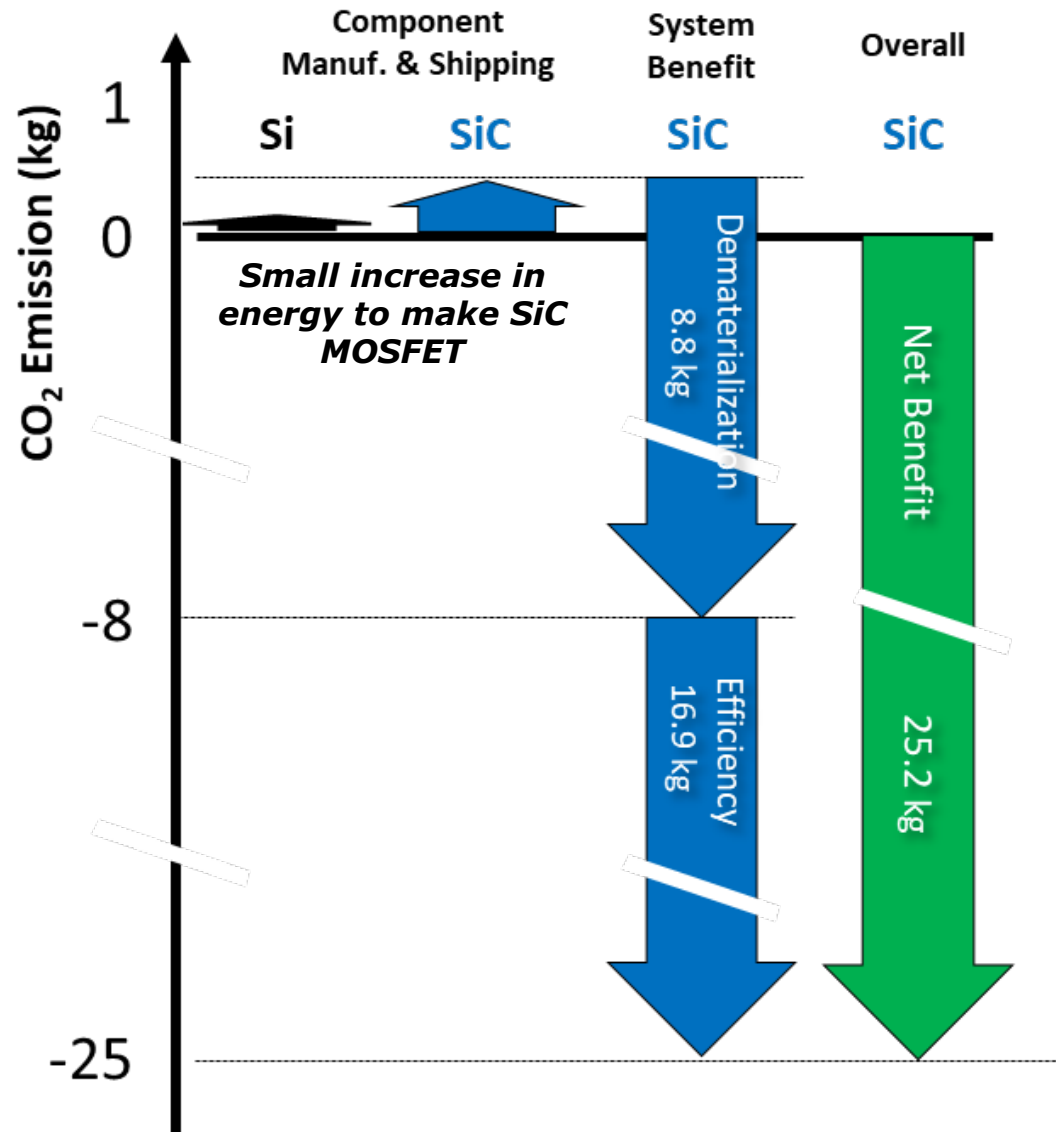
Competitor SiC
45 W system loss



T-A PG
40 W system loss
-30% SiC loss



Every T-A PG MOSFET Saves Over 25 kg CO₂



Huge benefit in application use



From EV Trucks to EVTOLs: Same Challenges, Same SiC Solutions



Battery Voltages: Archer 800V⁽¹⁾, Lilium 900V⁽²⁾ Joby 1000V⁽³⁾

Require SiC: 1,200V, 1,700V

1) <https://archer.com/technologies>

2) <https://lilium.com/newsroom-detail/first-high-voltage-electrical-harnesses-roll-off-the-line-for-the-all-electric-lilium-jet>

3) https://joby-site.cdn.prismic.io/joby-site/5f82ea34-645e-4468-8e3f-14a16e298941_Joby-Charging-GEACS-final.pdf



Thank you for your interest.

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Emerging Applications for Power Electronics

